



Docket No.: 8733.378.00-US
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Myoung-Su Yang

Application No.: 09/748,871

Filed: December 28, 2000

For: METHOD OF FORMING A
POLYCRYSTALLINE SILICON LAYER

Group Art Unit: 2812

Examiner: R. Pompey

#15/C
Amend
D. M. Hamilton
6/11/03
arg
9/25/03

AMENDMENT

Mail Stop AF
Commissioner of Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

In response to the Office Action dated March 27, 2003 (Paper No.14), please amend the above-identified U.S. patent application as follows:

IN THE CLAIMS

Please **AMEND** claims 1, 7, 18 and 19 as follows (marked up version of the claim change is attached):

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1. (Twice Amended) A method of forming a polycrystalline silicon layer, comprising:

forming an amorphous silicon layer on a substrate;

melting the amorphous silicon layer using a laser beam thereby forming the polycrystalline silicon layer using a mask; and

melting only an upper portion of the polycrystalline silicon layer using the laser beam with the mask thereby recrystallizing the upper portion of the polycrystalline silicon layer,